



ZHEJIANG UNIU-NE Technology CO., LTD

浙江宇力微新能源科技有限公司



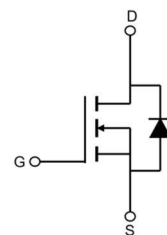
AP9N20K Data Sheet

V 1.1

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Feature

- 200V,9A
 $R_{DS(ON)} < 300m\Omega @ V_{GS}=10V$ TYP:250 m Ω
- Advanced Planar stripe DMOS Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram



Marking and pin assignment

Application

- PWM applications
- Load Switch
- Power management

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
9N20K	AP9N20K	TO-252	-	-	2500

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a=25^{\circ}C$)	I_D	9	A
Avalanche Current ⁽¹⁾	I_{AS}	5	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	36	A
Singel Pulsed Avalanche Energy ⁽²⁾	E_{AS}	115	mJ
Repetitive Avalanche Energy ⁽²⁾	E_{AR}	69	mJ
Power Dissipation	P_D	74	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.7	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	200	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =200V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ± 20V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	-	4.0	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =10V, I _D =4.5A	-	250	300	mΩ
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f =1.0MHz	-	605	-	pF
Output Capacitance	C _{oss}		-	87	-	
Reverse Transfer Capacitance	C _{rss}		-	37	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =100V, I _D =9A, V _{GS} =10V, R _G =25Ω	-	35	-	ns
Turn-on rise time	t _r		-	7	-	
Turn-off delay time	t _{d(off)}		-	98	-	
Turn-off fall time	t _f		-	32	-	
Total Gate Charge	Q _g	V _D S=160V, I _D =9A, V _G S=10V	-	19	-	nC
Gate-Source Charge	Q _{gs}		-	3	-	
Gate-Drain Charge	Q _{gd}		-	8	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} =0V, I _S =4.5A	-	-	1.4	V
Diode Forward current ⁽⁴⁾	I _S		-	-	9	A
Body Diode Reverse Recovery Time	trr	T _J =25° , IF=9A,di/dt=100A/us		145		ns
Body Diode Reverse Recovery Charge	Qrr	T _J =25° , IF=9A,di/dt=100A/us		0.82		uc

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: $T_J = 25^{\circ}\text{C}, V_{DD} = 50V, R_G = 50\Omega, L = 10mH$
3. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
4. Surface Mounted on FR4 Board, $t \leq 10\text{ sec}$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

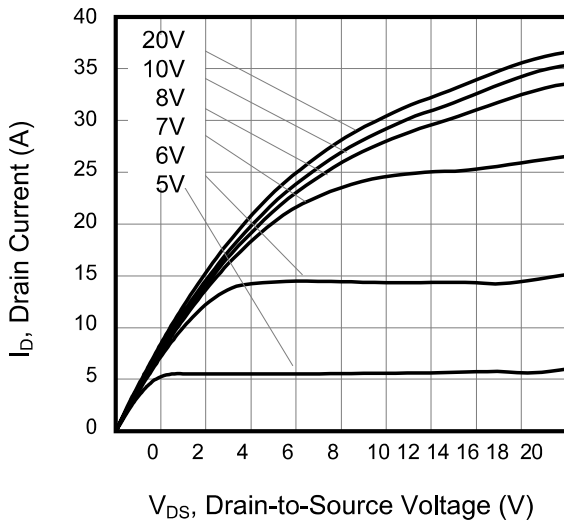


Figure 2. Body Diode Forward Voltage

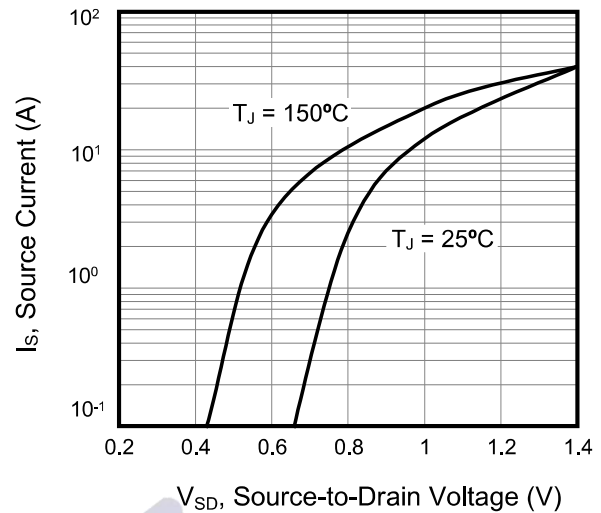


Figure 3. Drain Current vs. Temperature

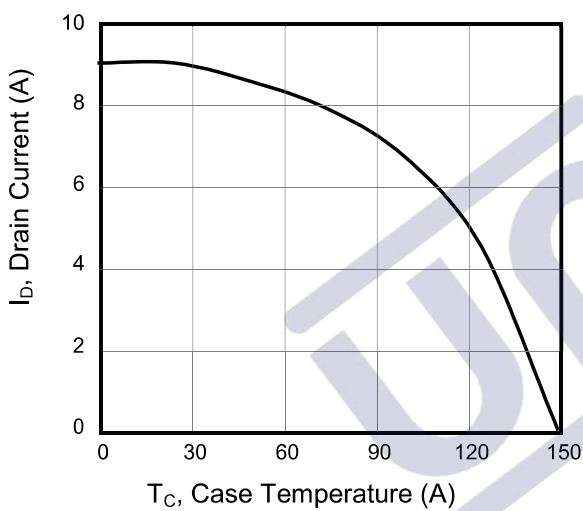


Figure 4. BV_{DSS} Variation vs. Temperature

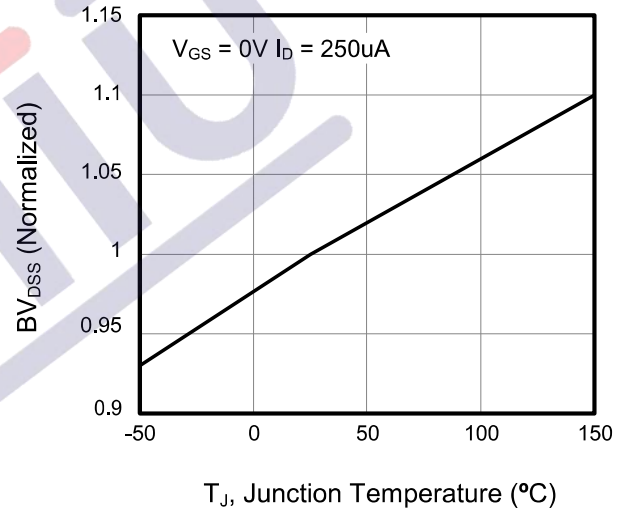


Figure 5. Transfer Characteristics

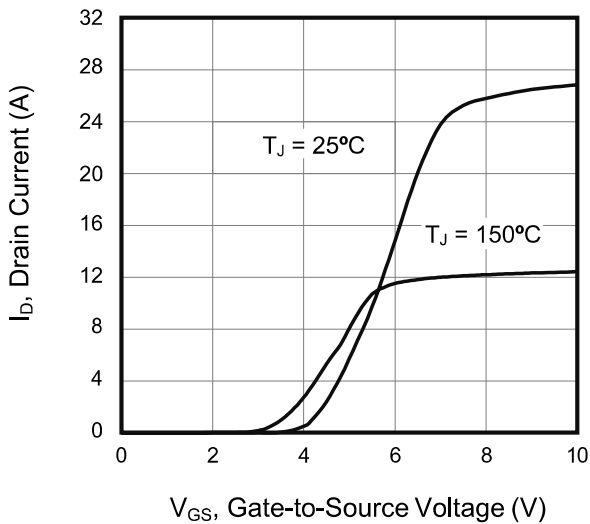
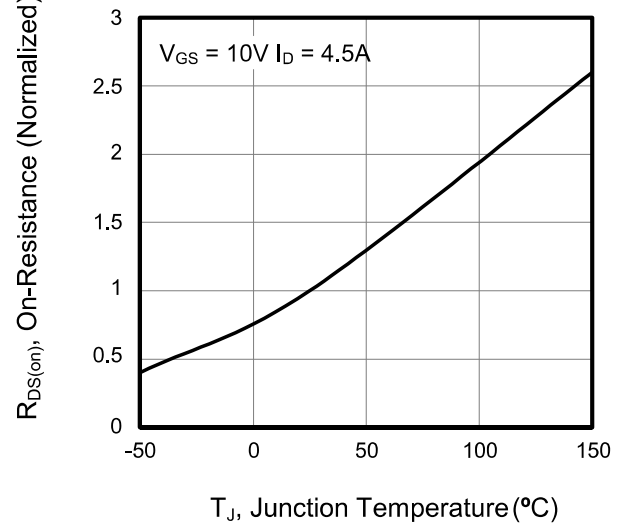


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

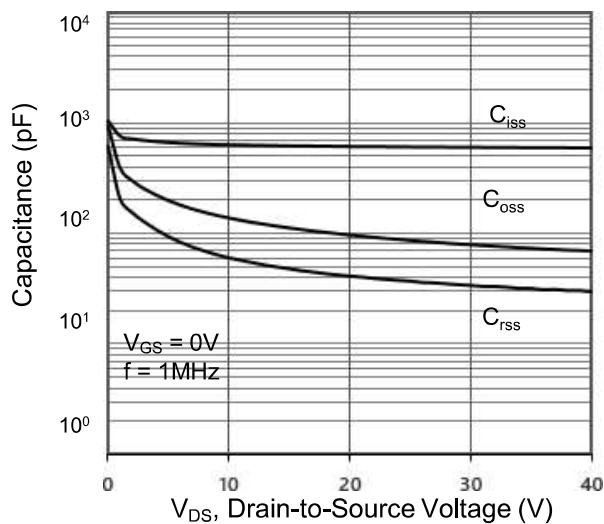


Figure 8. Gate Charge

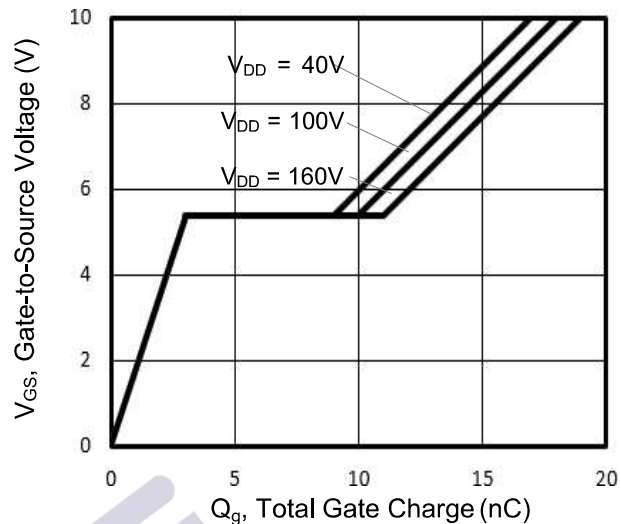


Figure 9. Transient Thermal Impedance TO-220F

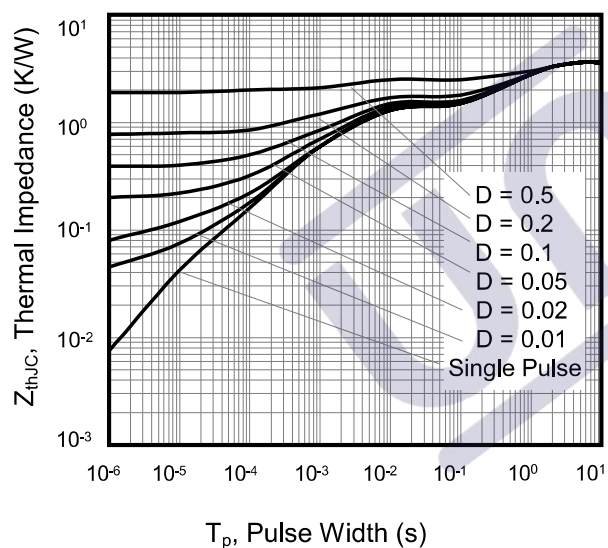


Figure 10. Transient Thermal Impedance TO-251, TO-252

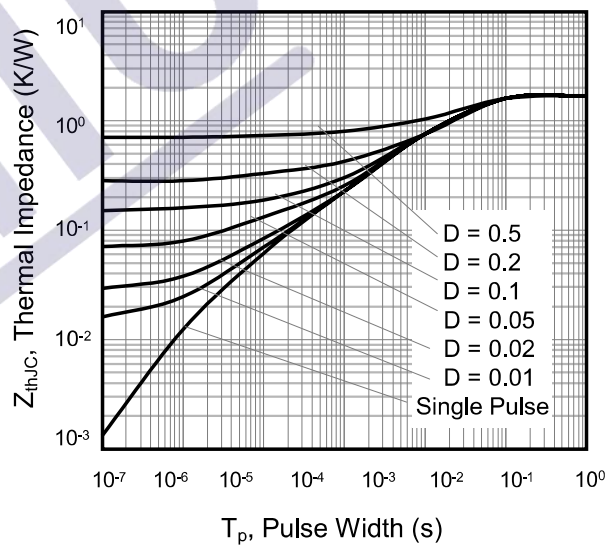


Figure A: Gate Charge Test Circuit and Waveform

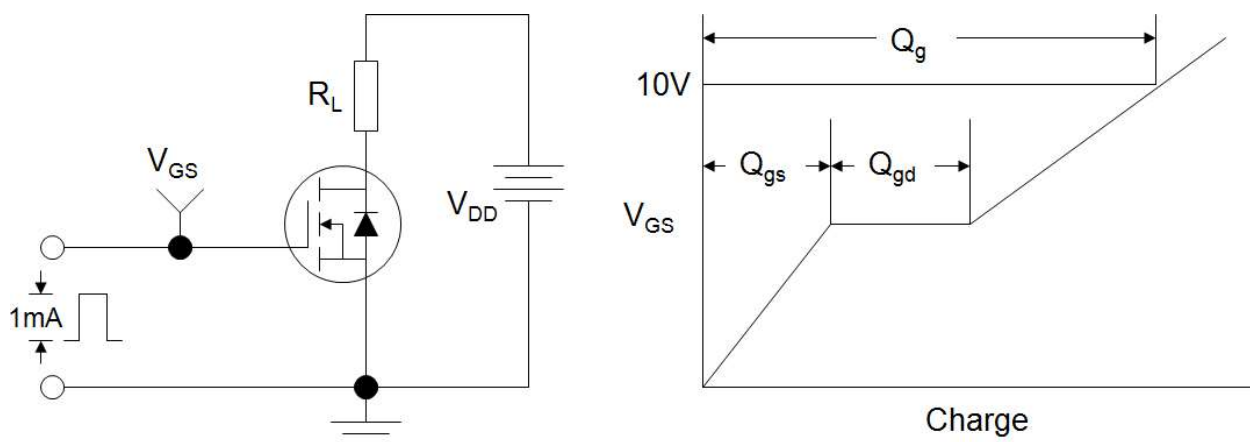


Figure B: Resistive Switching Test Circuit and Waveform

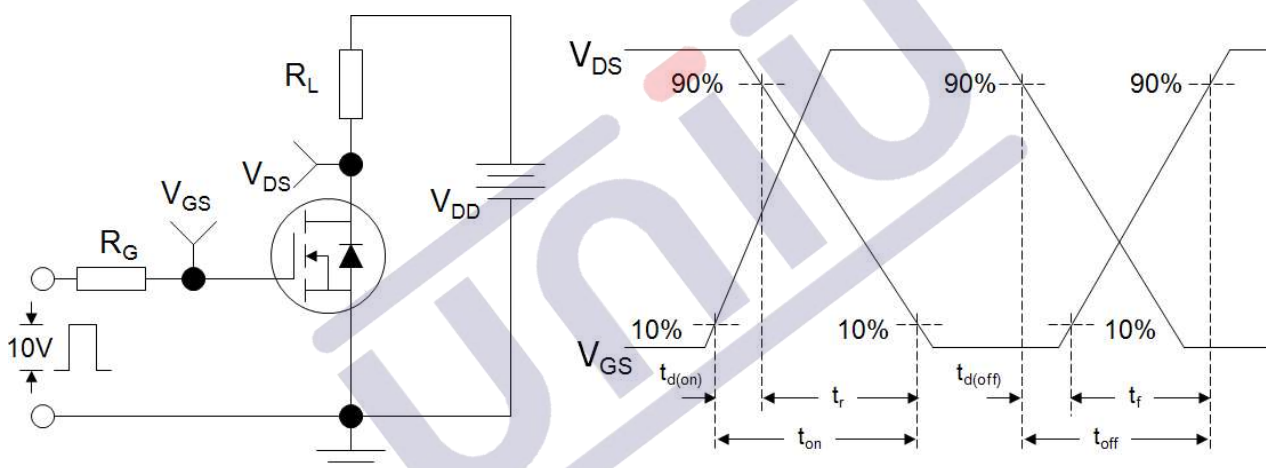
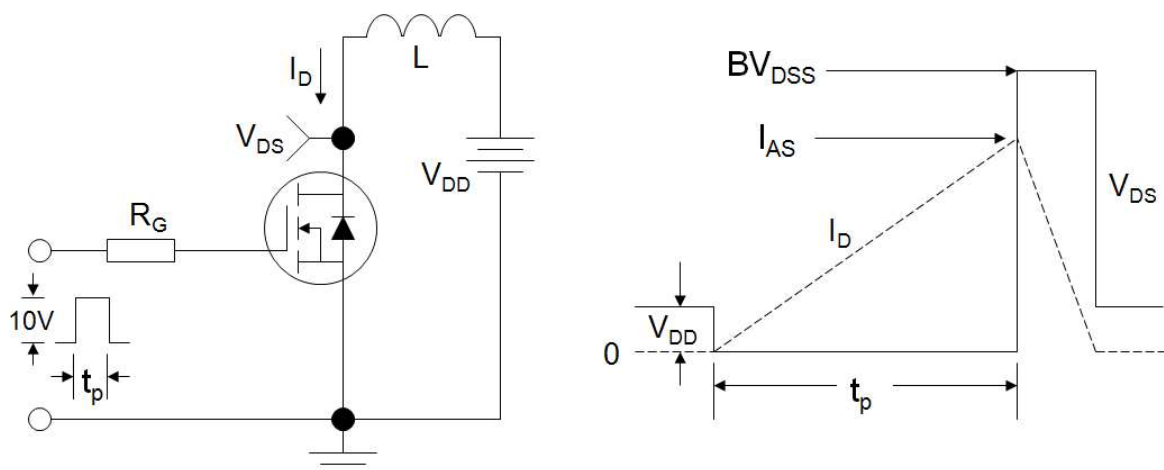
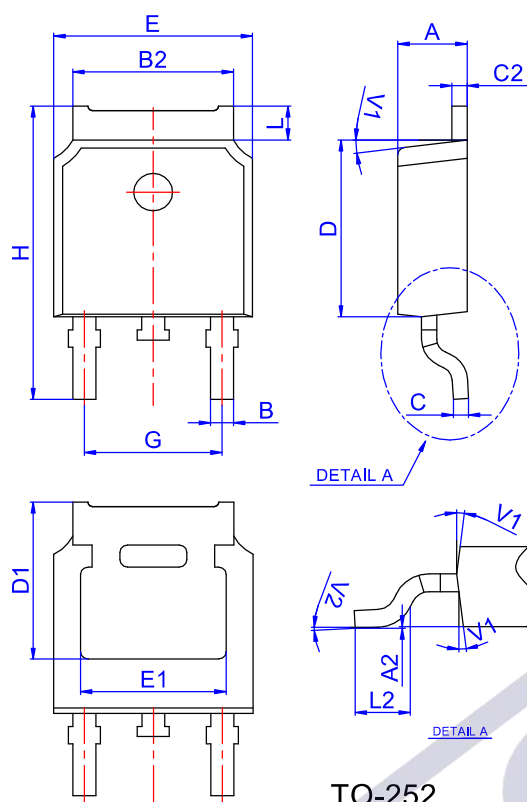


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



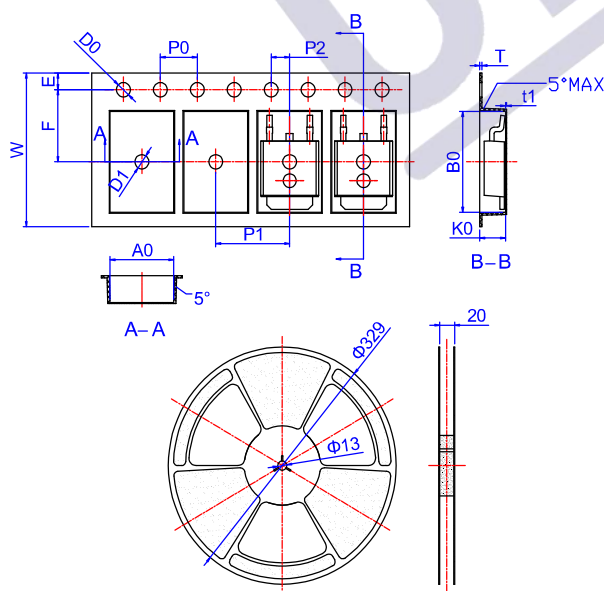
TO-252 Package Information



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

1.版本记录

DATE	REV.	DESCRIPTION
2018/04/19	1.0	First Release
2021/11/20	1.1	Layout adjustment

2.免责声明

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3.联系我们

浙江宇力微新能源科技有限公司

总部地址：绍兴市越城区斗门街道袍渚路25号中节能科创园45幢4/5楼

电话：0575-85087896（研发部）

传真：0575-88125157

E-mail: htw@uni-semic.com

无锡地址：无锡市锡山区先锋中路 6 号中国电子（无锡）数字芯城 1#综合楼 503室

电 话：0510-85297939

E-mail: zh@uni-semic.com

深圳地址：深圳市宝安区西乡街道南昌社区宝源路泳辉国际商务大厦410

电 话：0755-84510976

E-mail: htw@uni-semic.com